

P1 M.2 2280 NVMe/PCIe NAND Flash SSD

CT500P1SSD8, CT1000P1SSD8, CT2000P1SSD8

Features

- Micron[®] 3D QLC NAND Flash
- RoHS-compliant package
- NVMe/PCIe Gen3 x4 Interface
- Industry-standard, 512-byte sector size support
- NVMe low power states supported
- Native command queuing support with 256-command support
- NVMe-standard self-monitoring, analysis, and reporting technology (SMART) command set
- Power loss protection for data-at-rest
- Performance¹
 - Sequential 128KB READ: Up to 2000 MB/s
 - Sequential 128KB WRITE: Up to 1750 MB/s
- Reliability
- MTTF: 1.8 million device hours²
- Static and dynamic wear leveling
- Low power consumption
 - 100mW TYP³
- Endurance total bytes written (TBW) – Up to 400TB
- Capacity (unformatted): 500GB, 1000GB and 2000GB
- M.2, 22mm x 80mm form factor
- Operating Temperature
 - Commercial $(0^{\circ}C \text{ to } 70^{\circ}C)^4$
- Digitally Signed Firmware

- Notes: 1. Typical I/O performance numbers as measured fresh-out-of-the-box (FOB) using CrystalDisk-Mark with write cache enabled.
 - 2. The product achieves a mean time to failure (MTTF) based on population statistics not relevant to individual units.
 - 3. Active average power measured during execution of MobileMark[®] 2014
 - 4. Temperature is recorded and displayed at SMART offset 1, and is best read by the Crucial Storage Executive Software.

Warranty: Contact your sales representative for further information regarding the product, including product warranties.



Part Numbering Information

The SSD is available under Micron's Crucial brand in different configurations and densities. The chart below is a comprehensive list of options for the P1 series devices; not all options listed can be combined to define an offered product.

Figure 1: Part Number Chart





General Description

Micron's solid state drive (SSD) uses a single-chip controller with a NVMe/PCIe interface on the system side and 4-channels of Micron NAND Flash internally. The SSD integrates easily in existing storage infrastructures.

The SSD is designed to use the NVMe/PCIe interface efficiently during both READs and WRITEs while delivering bandwidth-focused performance. SSD technology enables enhanced boot times, faster application load times, reduced power consumption, and extended reliability.

Figure 2: Functional Block Diagram





Logical Block Address Configuration

The drive is set to report the number of logical block addresses (LBA) that will ensure sufficient storage space for the specified capacity. Standard LBA settings, based on the IDEMA standard (LBA1-03), are shown below.

Table 1: Standard LBA Settings

	Total LBA		Max L	User Available Bytes	
Capacity	Decimal	Hexadecimal	Decimal	Hexadecimal	(Unformatted)
500	976,773,168	3A386030	976,773,167	3A38602F	500,107,862,016
1000	1,953,525,168	74706DB0	1,953,525,167	74706DAF	1,000,204,886,016
2000	3,907,029,168	E8E088B0	3,907,029,167	E8E088AF	2,000,398,934,016



Physical Configuration

M.2 2280 (22mm x 80mm)

Product mass: less than 10 grams

Physical dimensions conform to the applicable form factor specifications as listed in the figure below.

Figure 3: M.2 Type 2280 Package



Notes: 1. All dimensions are in millimeters.

Table 2: M.2 Type 2280 Package Dimensions

Capacity (GB)	Specification	W	L	Α	В	С	Unit
500	57						
1000	32	22.00	80.00	1.35	0.80	1.50	mm
2000	D3						

Notes: 1. Dimension values in millimeter per SFF 8201 Rev. 3.3.



Interface Connectors

Figure 4: SSD Interface Connections M.2 Type 2280



Table 3: Signal Assignments

Top Side		Bottom Side			
Pin#	Signal Name	Description	Pin#	Signal Name	Description
1	GND	Ground	2	3.3V	+3.3V
3	GND	Ground	4	3.3V	+3.3V
5	PETn3	PCle TX– Lane 3	6	NC6	No connect
7	PETp3	PCle TX+ Lane 3	8	NC8	No connect
9	GND	Ground	10	DAS	Drive activity signal
11	PERn3	PCle RX– Lane 3	12	3.3V	+3.3V
13	PERp3	PCle RX+ Lane 3	14	3.3V	+3.3V
15	GND	Ground	16	3.3V	+3.3V
17	PETn2	PCle TX– Lane 2	18	3.3V	+3.3V
19	PETp2	PCle TX+ Lane 2	20	NC20	No connect
21	GND	Ground	22	NC22	No connect
23	PERn2	PCle RX– Lane 2	24	NC24	No connect
25	PERp2	PCIe RX+ Lane 2	26	NC26	No connect
27	GND	Ground	28	NC28	No connect
29	PETn1	PCle TX– Lane 1	30	NC30	No connect
31	PETp1	PCle TX+ Lane 1	32	NC32	No connect
33	GND	Ground	34	NC34	No connect
35	PERn1	PCle RX– Lane 1	36	NC36	No connect
37	PERp1	PCle RX+ Lane 1	38	NC38	No connect
39	GND	Ground	40	NC40	No connect
41	PETn0	PCle TX– Lane 0	42	NC42	No connect
43	PETp0	PCIe TX+ Lane 0	44	NC44	No connect
45	GND	Ground	46	NC46	No connect
47	PERn0	PCle RX– Lane 0	48	NC48	No connect
49	PERp0	PCIe RX+ Lane 0	50	PERST#	PERST#
51	GND	Ground	52	CLKREQ#	CLKREQ#



Table 3: Signal Assignments (Continued)

Top Side			Bottom Side			
Pin#	Signal Name	Description	Pin#	Signal Name	Description	
53	REFCLKn	PCIe REFCLK-	54	PEWAKE#	No connect	
55	REFCLKp	PCIe REFCLK+	56	MFG_DATA	Reserved	
57	GND	Ground	58	MFG_CLOCK	Reserved	
	Mechanical M Key		Mechanical M Key			
67	NC67	No Connect	68	SUSCLK	No connect	
69	PEDET	No Connect	70	3.3V	+3.3V	
71	GND	Ground	72	3.3V	+3.3V	
73	GND	Ground	74	3.3V	+3.3V	
75	GND	Ground	0	0	0	



Performance

Measured performance can vary for a number of reasons. The major factors affecting drive performance are the capacity of the drive, the host computer's storage controller and drivers. Additionally, overall system performance can affect the measured drive performance. When comparing drives, it is recommended that all system variables are held constant, with only the drive under test changing.

Performance numbers will also vary depending on the host system configuration, as CPU speed and memory configuration may affect storage performance.

For SSDs designed for the client computing market, Micron specifies performance in FOB ("fresh-out-of-box") state. Data throughput measured in "steady state" may be lower than FOB state, depending on the nature of the data workload.

For a description of these performance states and of Micron's best practices for performance measurement, refer to micron.com/ssd.

Table 4: Drive Performance

Capacity	500GB	1000GB	2000GB	
Interface		Unit		
Sequential read (128KB transfer)	1,900	2,000	2,000	MB/s
Sequential write (128KB transfer)	950	1,700	1,750	MB/s
Random read (4kB transfer)	90,000	170,000	250,000	IOPS
Random write (4kB transfer)	220,000	240,000	250,000	IOPS

Notes: 1. Performance numbers are maximum values.

- 2. Typical I/O performance numbers as measured using CrystalDiskMark® 6.0.1 with write cache enabled, a queue depth of 64 (QD = 8, Threads = 8). Fresh out-of-box (FOB) state is assumed. For performance measurement purposes, the SSD may be restored to FOB state using the secure erase command. System variations will affect measured results.
- **3.** Due to security concerns, computer manufacturers have introduced updates to BIOS firmware which can affect SSD performance as measured in common benchmark tests. Some of these tests have shown as much as a 20% to 25% decrease in performance, after the security changes are installed, especially for random transactions.



Reliability

Micron's SSDs incorporate advanced technology for defect and error management. They use various combinations of hardware-based error correction algorithms and firmware-based static and dynamic wear-leveling algorithms.

Mean Time To Failure

Mean time to failure (MTTF) for the SSD is predicted based on the component reliability data using the methods referenced in the Telcordia SR-332 reliability prediction procedures for electronic equipment, in addition to Micron's Reliability Demonstration Testing.

Table 5: MTTF

Capacity	MTTF (Operating Hours) ¹
500GB	
1000GB	1.8 million
2000GB	

Notes: 1. Mean time to failure (MTTF) is a statistic based on the total service hours of a large population of SSDs, and does not predict the lifetime of any individual unit.

Endurance

Endurance for the SSD can be predicted based on usage conditions applied to the device, the internal NAND component cycles, the write amplification factor, and the wear-leveling efficiency of the drive. The tables below show the drive lifetime for each SSD capacity by client computing and sequential input and based on predefined usage conditions.

Table 6: Drive Lifetime – Client Computing

Capacity	Drive Lifetime (Total Bytes Written)
500GB	100TB
1000GB	200TB
2000GB	400TB

Notes: 1. Total bytes written calculated with the drive 90% full.

- **2.** SSD volatile write cache is enabled. Access patterns used during reliability testing are 25% sequential and 75% random and consist of the following: 50% are 4KB; 40% are 64KB; and 10% are 128KB.
- **3.** GB/day can be estimated by dividing the total bytes written value by (365 × number of years). For example: 100TB/5 years/365 days = 54GB/day for 5 years.
- **4.** Host workload parameters, including write cache settings, I/O alignment, transfer sizes, randomness, and percent full, that are substantially different than the described notes may result in varied endurance results.



Electrical Characteristics

Environmental conditions beyond those listed may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Table 7: NVMe/PCIe Power Consumption

	NVMe Power	NVMe Power	NVMe Pov		
Capacity	State 4 Sleep (Typ)	State 3 Slumber (Max)	Idle Power (Max)	Sequential Writes (Max)	Unit
500GB	2	80	800	8,000	mW
1000GB	2	80	800	8,000	mW
2000GB	2	80	800	8,000	mW

Notes: 1. Data taken at 25°C using a NVMe/PCIe interface.

- 2. Active average power measured while running MobileMark Productivity Suite.
- 3. NVMe Low Power States supported.
- **4.** Active maximum power is measured using Iometer with 128KB sequential write transfers @QD64.

Table 8: Maximum Ratings

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
Voltage input, M.2	3V3	3.14	3.46	V	-
Operating temperature	Т _С	0	70	°C	1
Non-operating temperature	-	-40	85	°C	_
Rate of temperature change	-	-	20	°C/hour	-
Relative humidity (non-condensing)	-	5	95	%	-

Notes: 1. Operating temperature is best measured by reading the SSD's on-board temperature sensor, which is recorded in SMART data at Offset 1. SMART data is best read using the Crucial Storage Executive software.

Table 9: Shock and Vibration

Parameter/Condition	Specification		
Non-operating shock	1500G/0.5ms		
Non-operating vibration	5–800Hz @ 3.1G		



Compliance

Micron SSDs comply with the following:

- Micron Green Standard
- Built with sulfur resistant resistors
- CE (Europe): EN55032, EN55024 Class B, RoHS
- FCC: CFR Title 47, Part 15, Class B
- UL/cUL: approval to UL-60950-1, 2nd Edition, IEC 60950-1:2005 (2nd Edition); EN 60950-1 (2006) + A11:2009+ A1:2010 + A12:2011 + A2:2013
- BSMI (Taiwan): approval to CNS 13438 Class B, CNS 15663
 <u>http://www.crucial.com/usa/en/company-environmental</u>
- CM (Morocco): Approval to No. 2574.14 and No. 2573.14 of 16 July 2015
- RCM (Australia, New Zealand): AS/NZS CISPR32 Class B
- KC RRL (Korea): approval to KN32 Class B, KN 35 Class B

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 지역에서는 물론 모든지역에서 사용할 수 있습니다.

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- TUV (Germany): approval to IEC60950/EN60950
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- Reorient or relocate the receiving antenna.
- Increase the separation between the equipment and the receiver.
- Connect the equipment into an outlet on a circuit different from that to which the receiver is connected.
- Consult the dealer or an experienced radio/TV technician for help.



References

- NVM Express, Revision 1.3
- PCI Express Base Specification, Revision 3.0
- PCI Express M.2 Electromechanical Specification, Revision 1.0
- IDEMA Standard LBA 1-03



Revision History

Rev. A – 9/18

Initial release

Rev. B - 9/18

• Added random performance benchmark scores



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